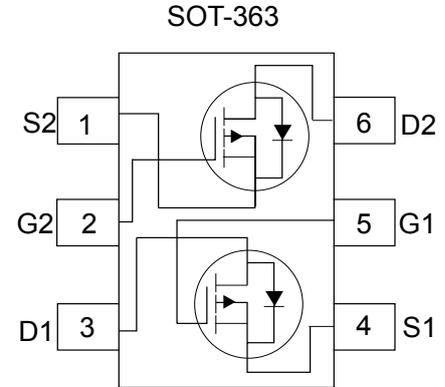


**Description**

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

MOSFET Product Summary		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (mA)
-20	0.45@ V <sub>GS</sub> =-4.5V	-800
	0.62@ V <sub>GS</sub> =-2.5V	
	0.86@ V <sub>GS</sub> =-1.8V	



**Absolute maximum rating@25°C**

Parameter	Symbol	Value	Units
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Continuous Drain Current	Continuous	I <sub>D</sub>	mA
	Pulsed	I <sub>DP</sub>	
Maximum Power Dissipation (Note 1)(Note 3)	P <sub>D</sub>	300	mW
Pulsed Drain Current(Note 2)	I <sub>DM</sub>	-1.2	A
Operating Junction Temperature	T <sub>J</sub>	150	°C
Lead Temperature	T <sub>L</sub>	260	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Units
Junction-to-Case Thermal Resistance	R <sub>θJA</sub>	-	-	415	°C/W

## Electrical characteristics per line@25°C( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$BV_{DSS}$	$I_D = -250\mu A, V_{GS} = 0V$	-20	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -16V, V_{GS} = 0V$	-	-	-1	$\mu A$
Gate-to-source Leakage Current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 8V$	-	-	$\pm 10$	$\mu A$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = -250\mu A$	-0.45	-0.55	-0.85	V
Drain-to-source On-resistance (Note4)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -700mA$	-	450	700	m $\Omega$
		$V_{GS} = -2.5V, I_D = -300mA$	-	620	850	m $\Omega$
		$V_{GS} = -1.8V, I_D = -250mA$	-	860	1200	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = -5V, I_D = -450mA$	-	1.25	-	S
<b>CHARGES, CAPACITANCES AND GATE RESISTANCE</b>						
Input Capacitance	$C_{ISS}$	$V_{GS} = 0V, V_{DS} = -10V,$ $f = 1MHz$	-	72	-	pF
Output Capacitance	$C_{OSS}$		-	9.5	-	pF
Reverse Transfer Capacitance	$C_{RSS}$		-	9.8	-	pF
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_D = -450mA$	-	0.9	-	nC
Threshold Gate Charge	$Q_{G(TH)}$		-	0.1	-	nC
Gate-to-Source Charge	$Q_{GS}$		-	0.15	-	nC
Gate-to-Drain Charge	$Q_{GD}$		-	0.3	-	nC
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_d(ON)$	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_D = -450mA$ $R_G = 6\Omega$	-	43	-	nS
Rise Time	$t_r$		-	137	-	nS
Turn-Off Delay Time	$t_d(OFF)$		-	1450	-	nS
Fall Time	$t_f$		-	2050	-	nS
<b>BODY DIODE CHARACTERISTICS</b>						
Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = -150mA$	-0.5	-0.65	-1.1	V

Note:

1. Surface mounted on FR4 board using minimum pad size, 1oz copper
2. Pulse width < 380 $\mu s$ , Single pulse
3. Maximum junction temperature  $T_J = 150^\circ C$ .
4. Pulse test: Pulse width < 380 us duty cycle < 2%.

Typical Characteristics

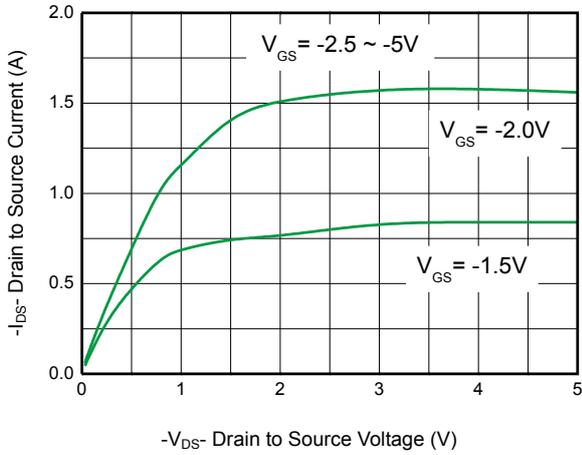


Fig 1. Output characteristics

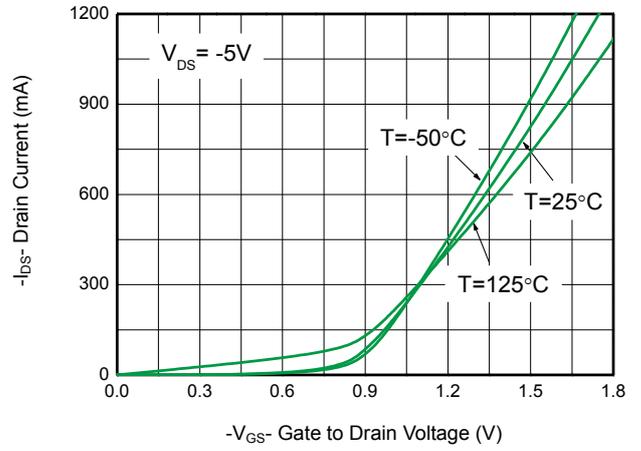


Fig 2. Transfer characteristics

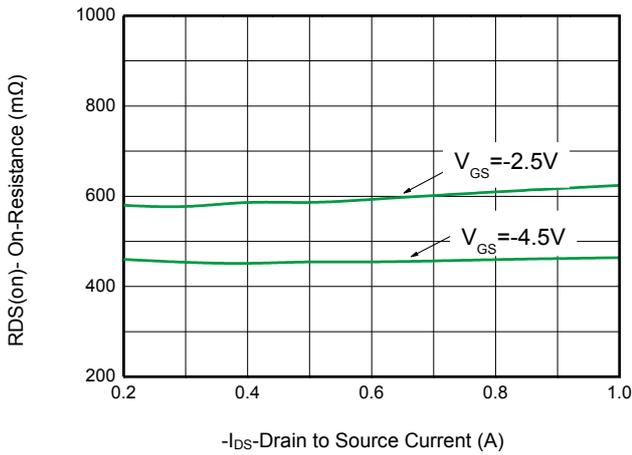


Fig 3. On-Resistance vs. Drain current

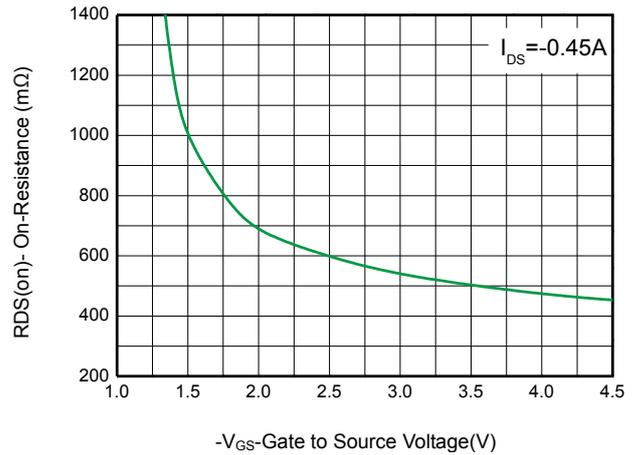


Fig 4. On-Resistance vs. Gate-to-Source voltage

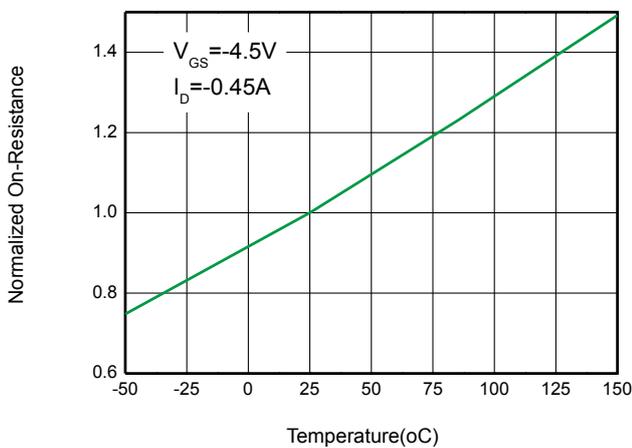


Fig 5. On-Resistance vs. Junction temperature

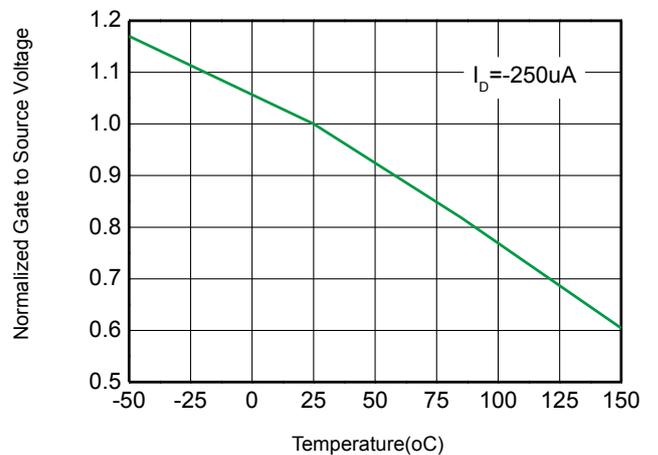


Fig 6. Threshold voltage vs. Temperature

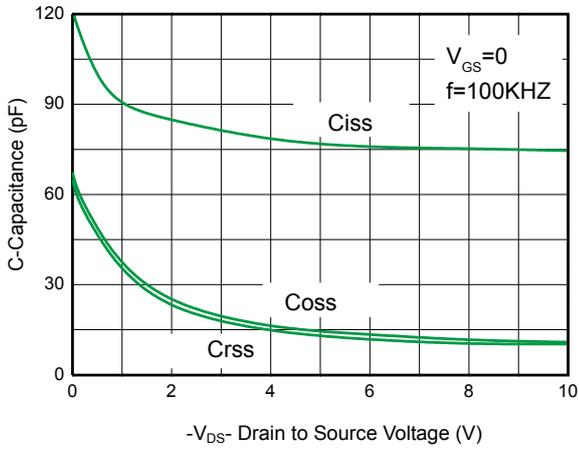


Fig 7. Capacitance.

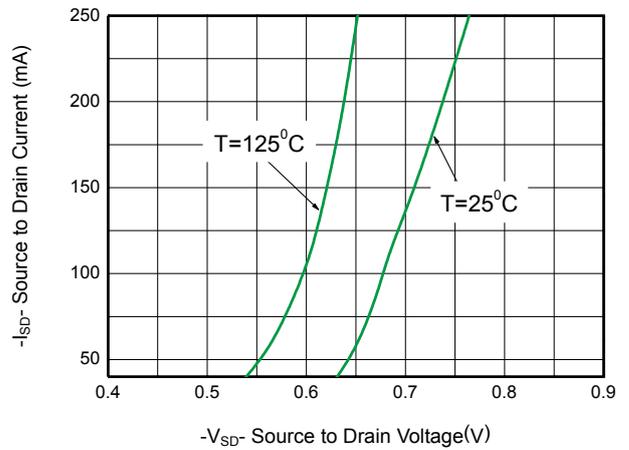


Fig 8. Body diode forward voltage

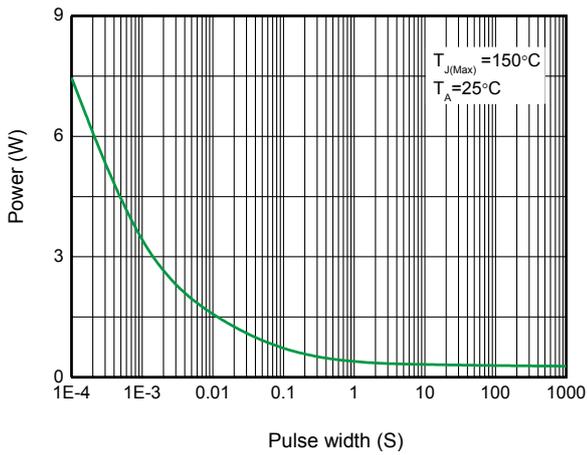


Fig 9. Single pulse power

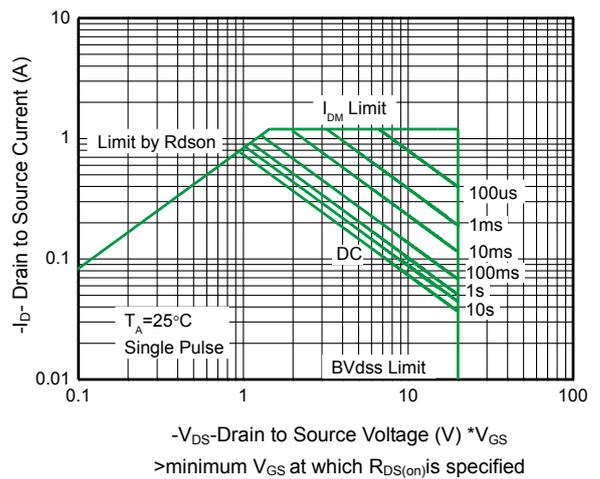


Fig 10. Safe operating power

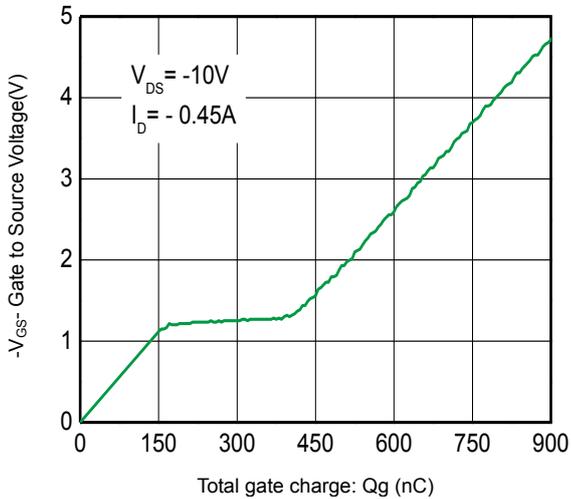
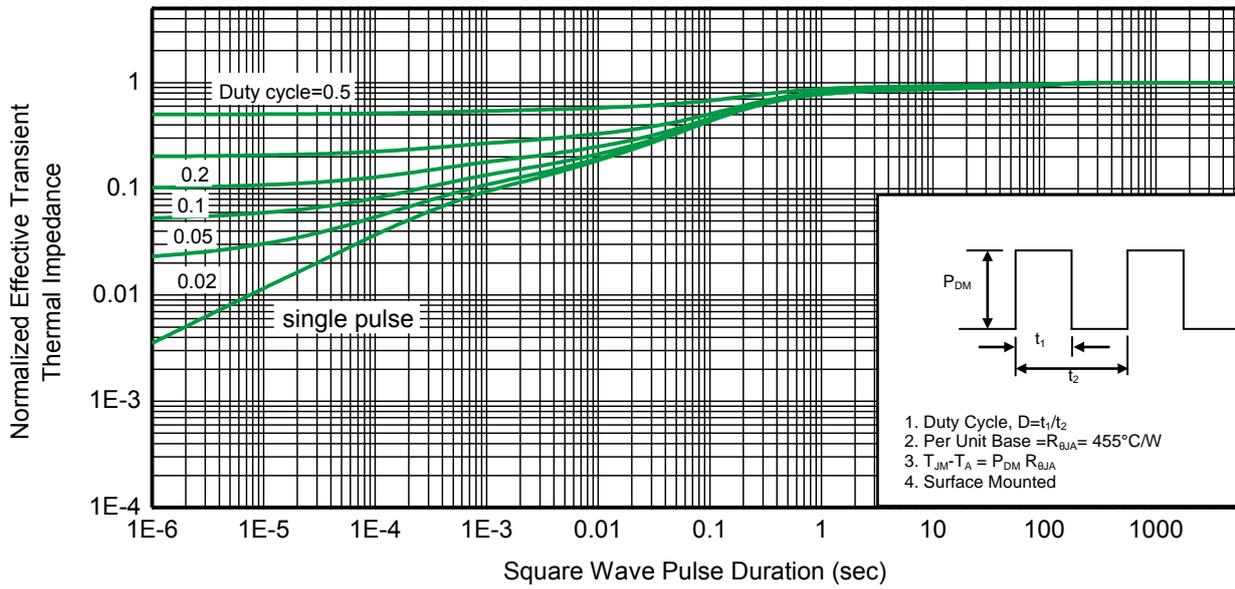
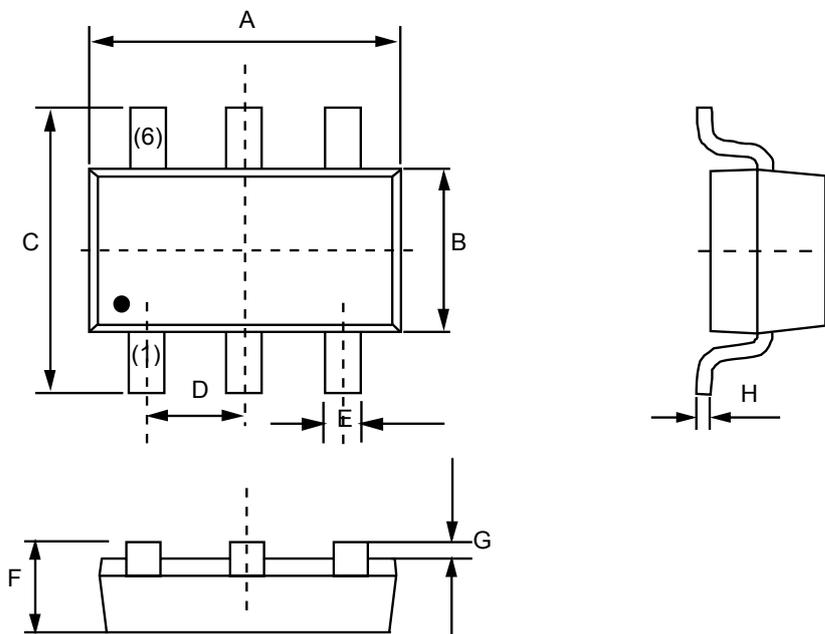


Fig 11. Dynamic input characteristics



Transient thermal response (Junction-to-Ambient)

Product dimension (SOT-363)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.0	2.2	0.079	0.087
B	1.15	1.35	0.045	0.053
C	2.15	2.45	0.085	0.096
D	0.65BSC		0.026BSC	
E	0.15	0.35	0.006	0.014
F	0.90	1.10	0.035	0.043
G	0.00	0.10	0.000	0.004
H	0.08	0.15	0.003	0.006

Ordering information

Device	Package	Shipping
PDPM6UT20V1E	SOT-363(Pb-Free)	3000 / Tape & Reel

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